



## AMENDED ABSTRACT

The present invention is a method for producing a single crystal by Czochralski method with pulling a seed crystal from a raw material melt, wherein ~~when~~ in which a range of a pulling rate of pulling a single crystal is defined as  $V$  (mm/min), ~~crystal~~, a temperature gradient at a solid-liquid interface is defined as  $G$  (K/mm) and a highest temperature at an interface between a crucible and a raw material melt is defined as  $T_{max}$  ( $^{\circ}\text{C}$ ), at least, a range of a value of  $V/G$  ( $\text{mm}^2/\text{K}\cdot\text{min}$ ) including a desired defect region and/or a desired defect-free region is determined according to the  $T_{max}$  ( $^{\circ}\text{C}$ ), and are defined. ~~the~~ The single crystal is pulled with controlling a value of  $V/G$  ( $\text{mm}^2/\text{K}\cdot\text{min}$ ) the pulling rate and/or the temperature gradient at a solid-liquid interface within the determined range. ~~There can be provided a~~ The method for producing a single crystal in which when produces a single crystal is pulled with controlling a value of  $V/G$ , a value of  $V/G$  including in which a desired defect region and/or a desired defect-free region can be determined more precisely and a single crystal with desired quality can be more surely pulled.